

/ Descriptions

KF \$0) E GE Silicon NPN transistor in a TO-92 Plastic Package.

/ Features

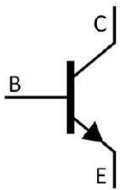
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High gain, good linearity of h_{FE} .

/ Applications

TV final picture IF amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Collector PIN 2 Emitter PIN 3 Base

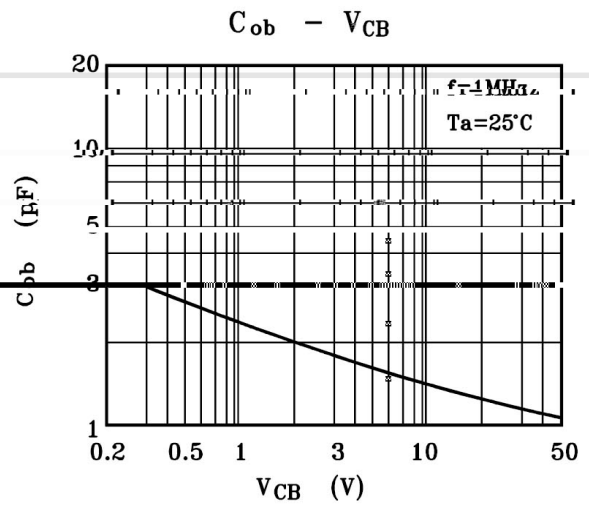
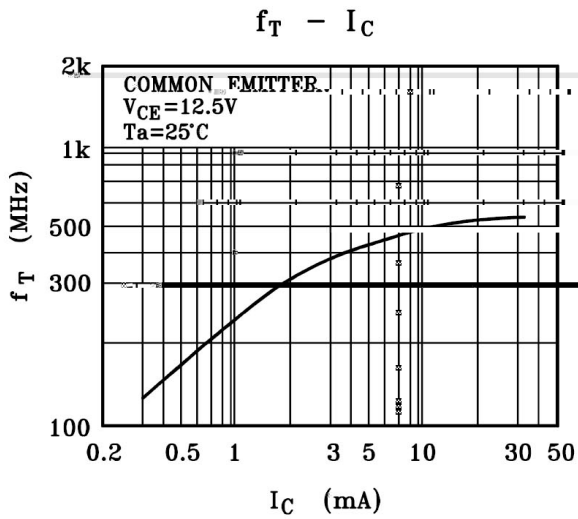
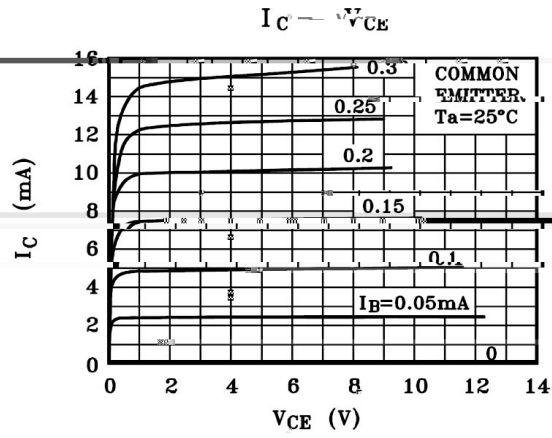
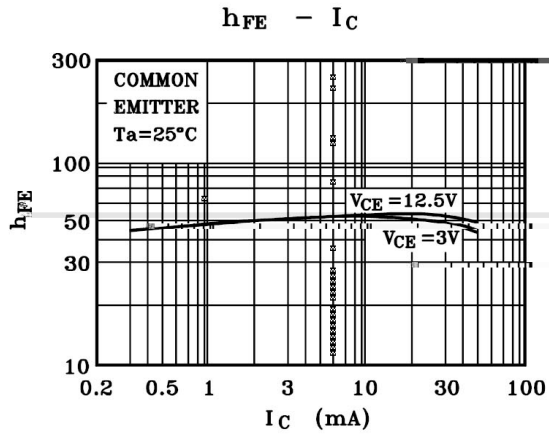
/ hFE Classifications & Marking

See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	25	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C	50	mA
Emitter Current - Continuous	I_E	-50	mA
Collector Power Dissipation	P_C	300	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=10mA$ $I_B=0$	25			V

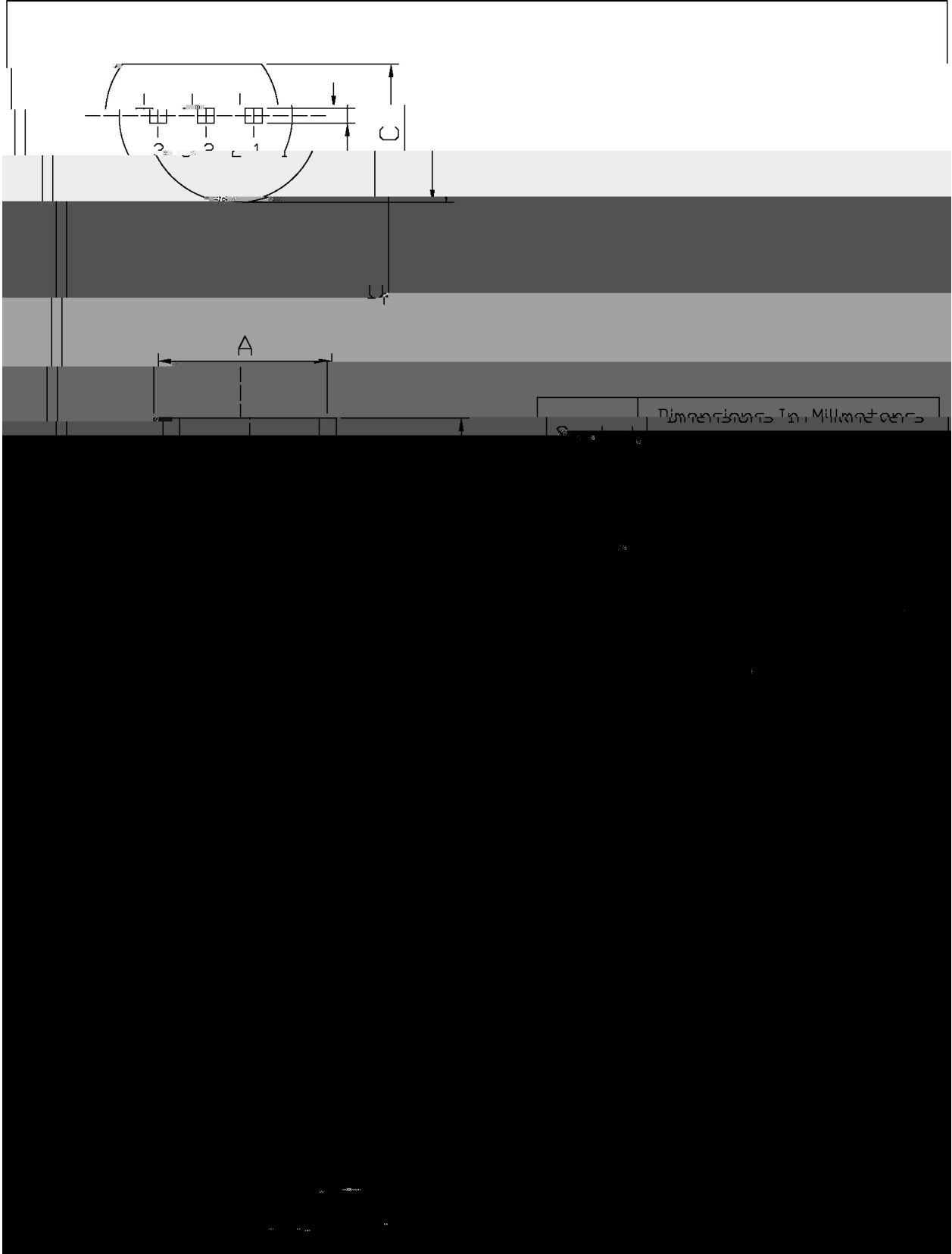
/ Electrical Characteristic Curve



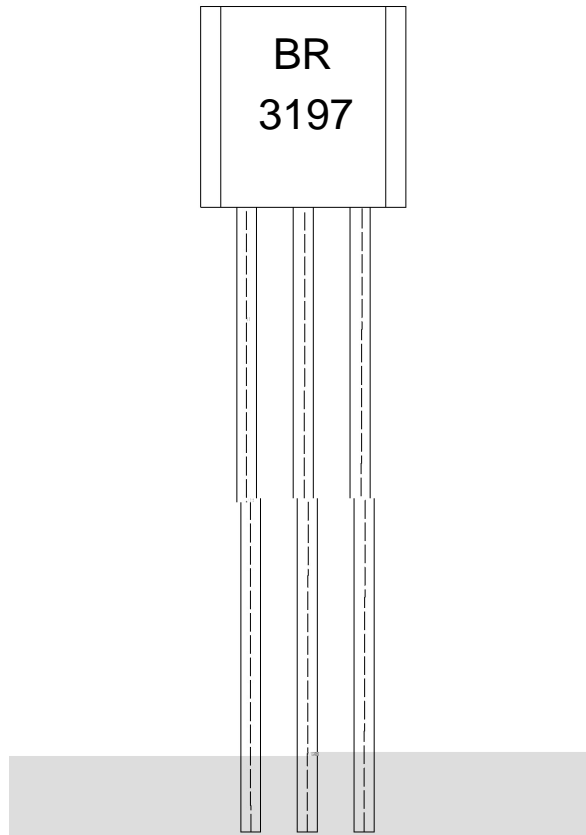
/ Package Dimensions

TO-92

Unit: mm



/ Marking Instructions



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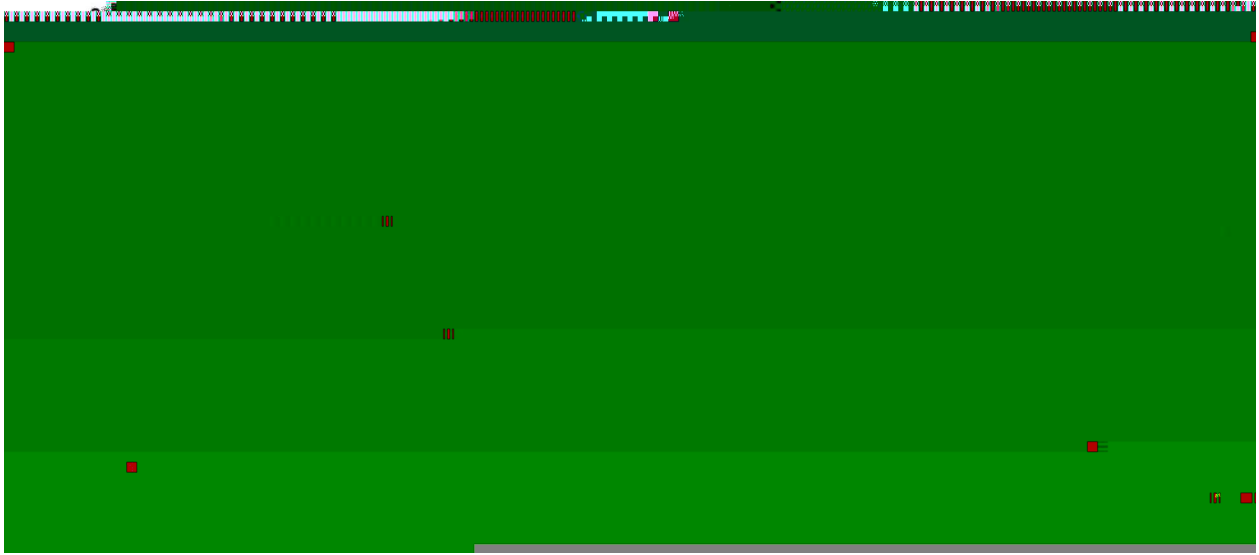
Note:

BR: Company Code.

3197: Product Type.

****: Lot No. Code,code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



1	25	150	60	90sec;	Note:	1.Preheating:25~150 , Time:60~90sec.
2	255..5		5..0.5sec;		2.Peak Temp.:255..5 , Duration:5..0.5sec.	
3		2	10	/sec.	3. Cooling Speed: 2~10 /sec.	

/ Resistance to Soldering Heat Test Conditions

270..5	10..1 sec.	Temp:270±5	Time:10±1 sec
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/ Packaging SPEC.

/ BULK